

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-25 (canceled)

Claim 26 (currently amended): An integrated circuit comprising a transistor, the transistor comprising:

a gate structure in a fixed relationship to a semiconductor active area and comprising a first sidewall and a second sidewall and thereby defining a first source/drain region adjacent the first sidewall and a second source/drain region adjacent the second sidewall; and

a lightly doped diffused region formed in a first portion of the first source/drain region and extending in a first region under a first portion of the gate structure, ~~wherein the lightly doped diffused region comprises a varying resistance in a direction parallel to the gate structure.~~ ; and

a second portion of the gate structure adjacent said first portion of the gate structure under which there is a second region comprising no lightly doped diffusion region, wherein said first and second regions comprises a varying resistance in a direction parallel to the gate structure.

Claim 27 (original): The integrated circuit of claim 26:

wherein the integrated circuit further comprises input/output circuitry and core circuitry; and

wherein the transistor is formed as part of the input/output circuitry.

Claim 28 (currently amended): The integrated circuit of claim 26:

wherein the integrated circuit further comprises a first plurality of transistors;

wherein the transistor comprises a first transistor in the first plurality of transistors;
wherein each transistor of the plurality of transistors comprises:

a gate structure in a fixed relationship to a semiconductor active area and comprising a first sidewall and a second sidewall and thereby defining a first source/drain region adjacent the first sidewall and a second source/drain region adjacent the second sidewall; and

a lightly doped diffused region formed in the first source/drain region and extending under the gate structure, wherein the lightly doped diffused region comprises a portion of a varying resistance in a direction parallel to the gate structure.

Claim 29 (original): The integrated circuit of claim 28:

wherein the integrated circuit further comprises input/output circuitry and core circuitry; and

wherein the plurality of transistors are formed as part of the input/output circuitry.

Claim 30 (currently amended): The integrated circuit of claim 28 wherein each transistor of the plurality of transistors further comprises a lightly doped diffused region formed in the second source/drain region and extending under the gate structure, wherein the lightly doped diffused region formed in the second source/drain region comprises a portion of a varying resistance in a direction parallel to the gate structure.

Claim 31 (original): The integrated circuit of claim 28:

wherein the integrated circuit further comprises input/output circuitry and core circuitry; and

wherein the plurality of transistors are formed as part of the input/output circuitry.

Amendments to the Drawings:

None